

COMPLEMENTARY SILICON HIGH-POWER TRANSISTORS

General Purpose-Amplifier and Switching Application..

FEATURES:

- * Collector-Emitter Sustaining Voltage -
 $V_{CE(sus)} = 120V$ (Min)- TIP31D, TIP32D
 $140V$ (Min)- TIP31E, TIP32E
 $160V$ (Min)- TIP31F, TIP32F
- * Current Gain-Bandwidth Product-
 $f_T = 3.0MHz$ (Min) @ $I_C = 1.0 A$

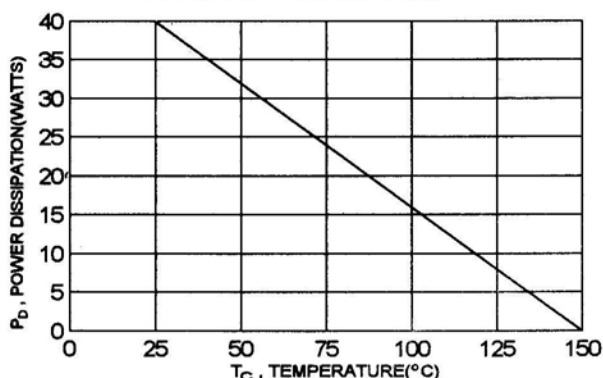
MAXIMUM RATINGS

Characteristic	Symbol	TIP31D TIP32D	TIP31E TIP32E	TIP31F TIP32F	Unit
Collector-Emitter Voltage	V_{CEO}	120	140	160	V
Collector-Base Voltage	V_{CBO}	160	180	200	V
Emitter-Base Voltage	V_{EBO}	5.0			V
Collector Current - Continuous - Peak	I_C	3.0 5.0			A
Base Current	I_B	1.0			A
Total Power Dissipation @ $T_C = 25^\circ C$ Derate above $25^\circ C$	P_D	40 0.32			W W/ $^\circ C$
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-65 to +150			$^\circ C$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	3.125	$^\circ C/W$

FIGURE -1 POWER DERATING



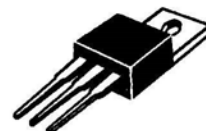
NPN PNP

TIP31D TIP32D

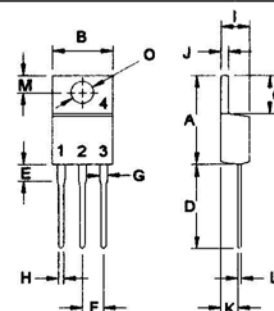
TIP31E TIP32E

TIP31F TIP32F

3.0 AMPERE
COMPLEMENTARY SILICON
POWER TRANSISTORS
120-160 VOLTS
40 WATTS



TO-220



PIN 1.BASE
2.COLLECTOR
3.EMITTER
4.COLLECTOR(CASE)

DIM	MILLIMETERS	
	MIN	MAX
A	14.68	16.00
B	9.78	10.42
C	5.02	6.60
D	13.00	14.62
E	3.10	4.19
F	2.41	2.67
G	1.10	1.67
H	0.69	1.01
I	3.21	4.98
J	1.14	1.40
K	2.20	3.30
L	0.28	0.61
M	2.48	3.00
O	3.50	4.00

TIP31D,TIP31E,TIP31F NPN / TIP32D,TIP32E,TIP32F PNP

ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector -Emitter Breakdown Voltage (1) ($I_C = 30\text{ mA}, I_B = 0$)	TIP31D,TIP32D TIP31E,TIP32E TIP31F,TIP32F	$V_{(BR)CEO}$	120 140 160	V
Collector Cutoff Current ($V_{CE} = 90\text{ V}, I_B = 0$)		I_{CEO}	0.3	mA
Collector Cutoff Current ($V_{CE} = 160\text{ V}, V_{BE} = 0$) ($V_{CE} = 180\text{ V}, V_{BE} = 0$) ($V_{CE} = 200\text{ V}, V_{BE} = 0$)	TIP31D,TIP32D TIP31E,TIP32E TIP31F,TIP32F	I_{CES}	0.2 0.2 0.2	mA
Emitter-Base Cutoff Current ($V_{EB} = 5.0\text{ V}, I_C = 0$)		I_{EBO}	1.0	mA

ON CHARACTERISTICS (1)

DC Current Gain ($I_C = 1.0\text{ A}, V_{CE} = 4.0\text{ V}$) ($I_C = 3.0\text{ A}, V_{CE} = 4.0\text{ V}$)	h_{FE}	25 5.0		
Collector-Emitter Saturation Voltage ($I_C = 3.0\text{ A}, I_B = 750\text{ mA}$)	$V_{CE(sat)}$		2.5	V
Base-Emitter On Voltage ($I_C = 3.0\text{ A}, V_{CE} = 4.0\text{ V}$)	$V_{BE(on)}$		1.8	V

DYNAMIC CHARACTERISTICS

Current-Gain-Bandwidth Product ($I_C = 0.5\text{ A}, V_{CE} = 10\text{ V}, f = 1.0\text{ MHz}$)	f_T	3.0		MHz
Small-Signal Current Gain ($I_C = 0.5\text{ A}, V_{CE} = 10\text{ V}, f = 1.0\text{ KHz}$)	h_{fe}	20		

SWITCHING CHARACTERISTICS

Turn On Time	$I_C = 1.0\text{ A}, I_{B1} = -I_{B2} = 0.1\text{ A}$	t_{on}	0.6	us
Off Time	$V_{BE(off)} = -4.3\text{ V}, R_L = 30\Omega$	t_{off}	2.8	us

(1) Pulse Test: Pulse width $\leq 300\text{ us}$, Duty Cycle $\leq 2.0\%$

(2) $f_T = |h_{fe}| \cdot f_{TEST}$

FIGURE 2 – SWITCHING TIME EQUIVALENT CIRCUIT

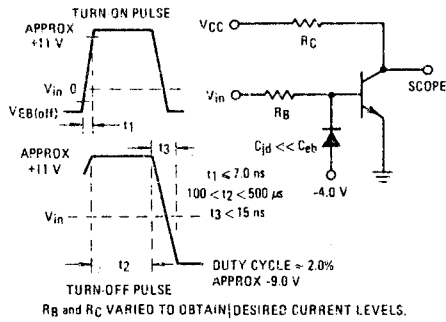


FIG-3 TURN-ON TIME

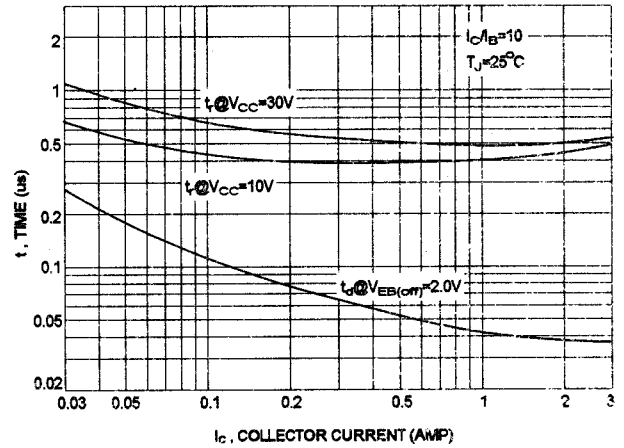


FIG-4 DC CURRENT GAIN

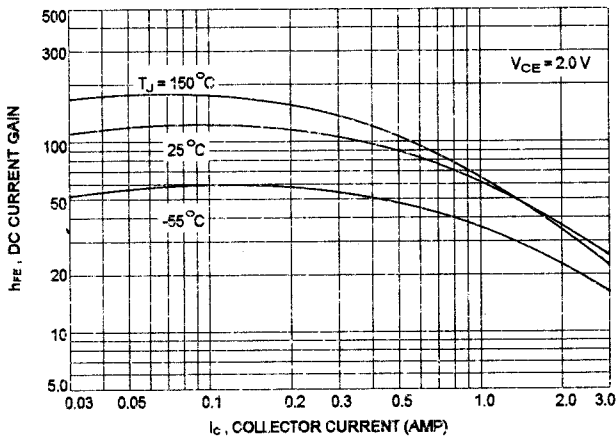


FIG-5 TURN-OFF TIME

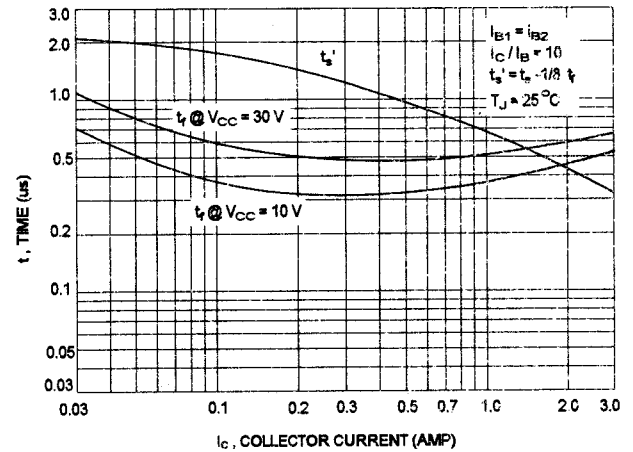
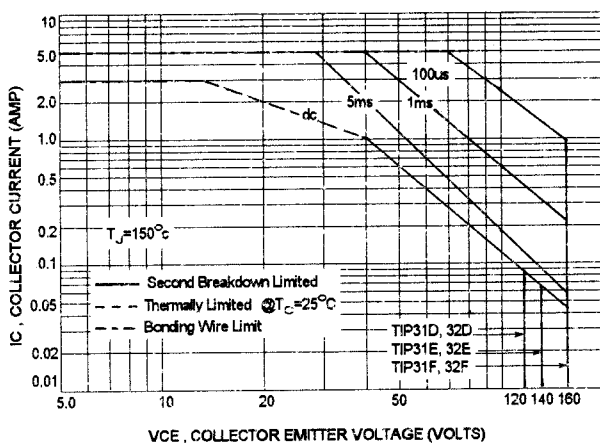


FIG-6 ACTIVE REGION SAFE OPERATING AREA



There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of FIG-6 curve is base on $T_{J(PK)} = 150^\circ\text{C}$; T_C is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(PK)} \leq 150^\circ\text{C}$. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

FIG-7 COLLECTOR SATURATION REGION

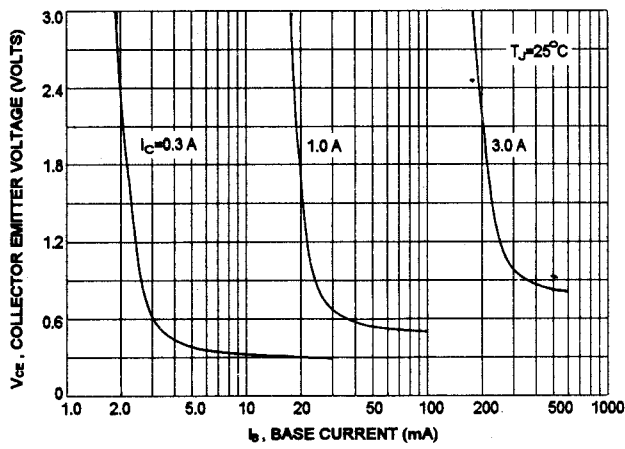


FIG-8 CAPACITANCES

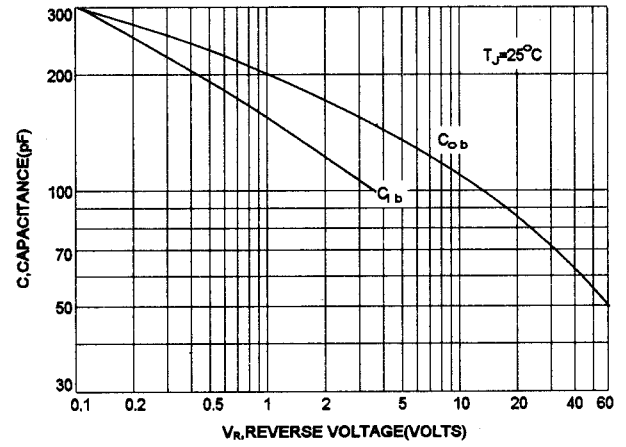


FIG-9 "ON" VOLTAGE

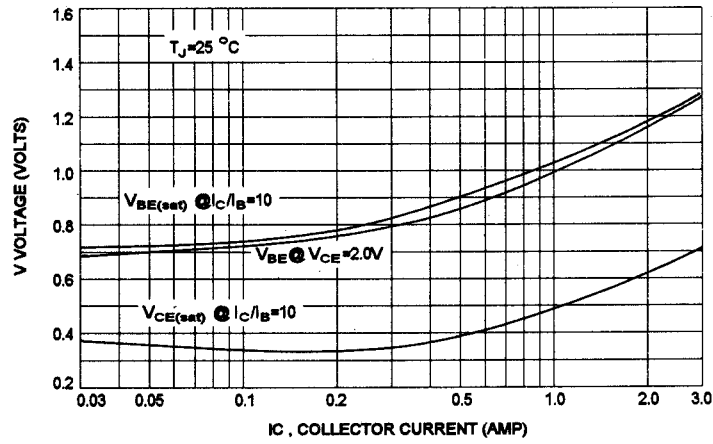
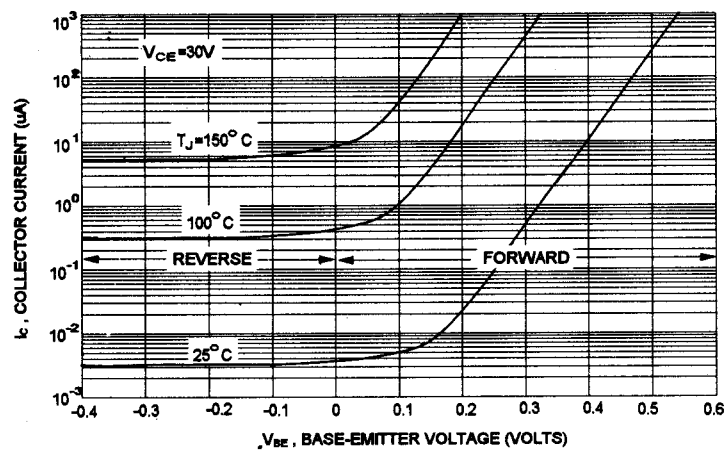


FIG-10 COLLECTOR CUT-OFF REGION



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